

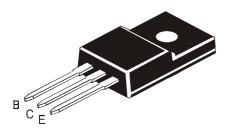
## Continental Device India Limited

An ISO/TS 16949, ISO 9001 and ISO 14001 Certified Company





#### SILICON PLANAR POWER DARLINGTON TRANSISTORS



NPN PNP CJF100 CJF105 CJF101 CJF106 CJF102 CJF107

TO-220FP Fully Isolated Plastic Package

# **Power Darlington for Linear and Switching Applications**

#### **ABSOLUTE MAXIMUM RATINGS**

DESCRIPTION	SYMBOL	CJF100 CJF105	CJF101 CJF106	CJF102 CJF107	UNIT
Collector Base Voltage	V <sub>CBO</sub>	60	80	100	V
Collector Emitter Voltage	V <sub>CEO</sub>	60	80	100	V
Emitter Base Voltage	V <sub>EBO</sub>	5.0			V
RMS Isolation Voltage (for 1sec, R.H.	(1) V <sub>ISOL</sub> (a)	3500			$V_{RMS}$
<30%, T <sub>A</sub> =25°C )	(b)	1500			
Collector Current - Continuous	I <sub>C</sub>	8.0			Α
Peak	I <sub>CM</sub>		15		
Base Current	l <sub>B</sub>	1.0			Α
Total Power Dissipation @ T <sub>c</sub> =25°C	P <sub>tot</sub>	80			W
Derate Above 25°C		0.64			W/°C
Total Power Dissipation @ T <sub>A</sub> =25°C	P <sub>tot</sub>	2.0			W
Derate Above 25°C			0.016		W/°C
Operating And Storage Junction	T <sub>j</sub> , T <sub>stg</sub>		- 65 to +150	)	°C
Temperature Range					

<sup>(1)</sup> RMS Isolation Voltage : (a) 3500 V<sub>RMS</sub> with Package in Clip Mounting Position (b) 1500 V<sub>RMS</sub> with Package in Screw Mounting Position (for 1sec, R.H.<30%Ta=25°C; Pulse Test: Pulse Width </=300µs, Duty Cycle</=2%)

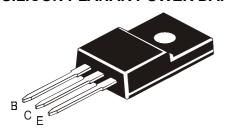
## THERMAL RESISTANCE

Characteristics	SYMBOL	MAX	UNIT
From Junction to Ambient	$R_{th(j-a)}$	62.5	°C/W
From Junction to Case	R <sub>th(j-c)</sub>	1.56	°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Collector Emitter Sustaining Voltage	V <sub>CEO (sus)</sub> *	I <sub>C</sub> =30mA, I <sub>B</sub> =0 CJF100/105 CJF101/106 CJF102/107	60 80 100	- - -	V V
Collector Cut Off Current	I <sub>CEO</sub>	V <sub>CE</sub> = I/2 Rated V <sub>CEO</sub> , I <sub>B</sub> =0	-	50	μΑ
	I <sub>CBO</sub>	V <sub>CB</sub> = Rated V <sub>CBO</sub> , I <sub>E</sub> =0	-	50	μA
Emitter Cut Off Current	I <sub>EBO</sub>	$V_{EB}$ =5V, $I_{C}$ =0	-	8.0	mA

## SILICON PLANAR POWER DARLINGTON TRANSISTORS



NPN PNP CJF100 CJF105 CJF101 CJF106 CJF102 CJF107

**TO-220FP Fully Isolated Plastic Package** 

# ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT	
Collector Emitter Saturation Voltages	V <sub>CE (sat)</sub> *	I <sub>C</sub> =3A, I <sub>B</sub> =6mA	-	2.0	V	
_	, ,	$I_C=8A$ , $I_B=80mA$	-	2.5		
Base Emitter On Voltage	V <sub>BE (on)</sub> *	Ե=8A, V <sub>CE</sub> =4V	-	2.8	V	
DC Current Gain	h <sub>FE</sub> *	I <sub>C</sub> =3A, V <sub>CE</sub> =4V	1000	20000		
		$I_C=8A, V_{CE}=4V$	200	_		

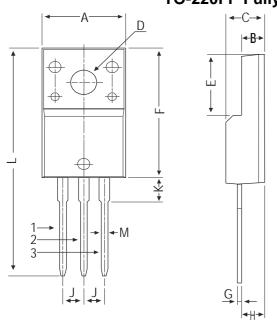
## **DYNAMIC CHARACTERISTICS**

Small Signal Current Gain	lh <sub>fe</sub> l	I <sub>C</sub> =3A, V <sub>CE</sub> =4V,f=1MHz	4.0	-	
Output Capacitance	$C_o$ $V_{CB}$ =10V, $I_E$ =0, f=0.1MHz				
		PNP	-	300	pF
		NPN	-	200	
Forward Voltage of Commutation Diode	V <sub>F</sub> *	I <sub>F</sub> = - I <sub>C</sub> =10A, I <sub>B</sub> =0	-	6.0	V

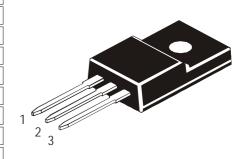
<sup>\*</sup> Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2 %

**CJF100 CJF105** CJF101 CJF106 CJF102 CJF107

# **TO-220FP Fully Isolated Plastic Package**



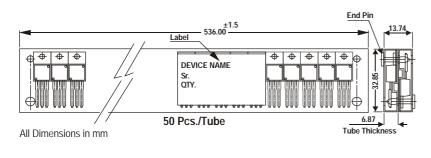
DIM	MIN	MAX				
А	9.80	10.36				
В	2.50	3.00				
С	4.30	4.90				
D	3.10	3.40				
Е	6.50	8.20				
F	14.80	17.27				
G	0.40	0.70				
Н	2.50	2.96				
J	2.34	2.74				
K	_	4.70				
L	_	30.05				
М	0.6	0.90				
All diminsions in mm.						

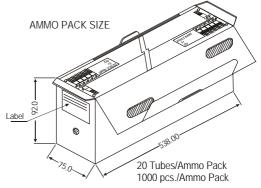


Pin Configuration

- Base
  Collector
- 3. Emitter

# **TO-220 FP Tube Packing**





# **Packing Detail**

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size Oty		Size	Oty	Gr Wt
TO-220FP	200 pcs/polybag	396 gm/200 pcs	3" x 7.5" x 7.5"	1K	17" x 15" x 13.5"	16K	36 kgs
	50 pcs/tube	135 gm/50 pcs	3.5" x 3.7" x 21.5"	1K	19" x 19" x 19"	10K	28 kgs

Notes

NPN PNP CJF100 CJF105 CJF101 CJF106 CJF102 CJF107

# **Component Disposal Instructions**

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

#### **Disclaimer**

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C-120 Naraina Industrial Area, New Delhi 110 028, India. Telephone + 91-11-2579 6150, 4141 1112 Fax + 91-11-2579 5290, 4141 1119

email@cdil.com www.cdilsemi.com

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